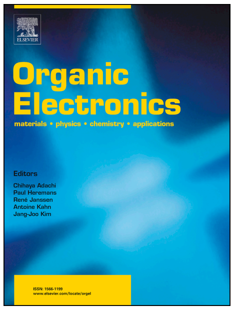

Scanning Kelvin Probe Microscopy investigation of the contact resistances and charge mobility in n-type PDIF-CN_2 thin-film transistors

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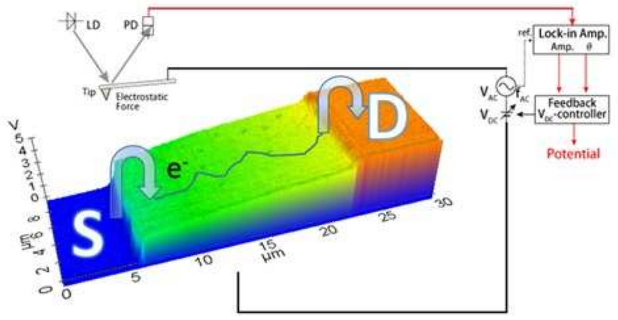
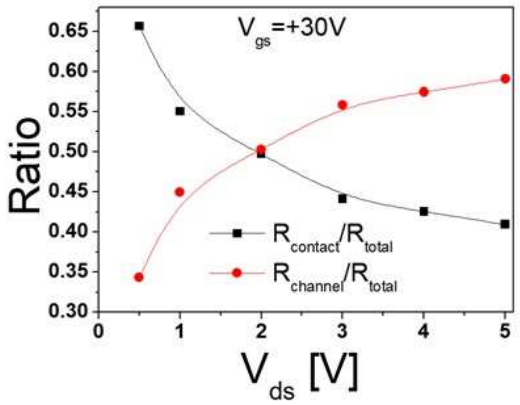

LD
PD
Tip
Electrostatic Force
ref.
Lock-in Amp.
Amp.
θ
V_{AC}
f_{AC}
V_{DC}
Feedback
V_{DC}-controller
Potential
V
5
4
3
2
1
0
μm
8
6
4
2
0
S
e⁻
D
0
5
10
15
20
25
30
μm


V_{gs}=+30V
Ratio
0.65
0.60
0.55
0.50
0.45
0.40
0.35
0.30
0
1
2
3
4
5
V_{ds} [V]
$R_{contact}/R_{total}$
$R_{channel}/R_{total}$